

# DATA SHEET

## **BUT11; BUT11A** Silicon diffused power transistors

Product specification  
Supersedes data of February 1996  
File under Discrete Semiconductors, SC06

1997 Aug 13

# Silicon diffused power transistors

# BUT11; BUT11A

### DESCRIPTION

High-voltage, high-speed, glass-passivated NPN power transistor in a TO-220AB package.

### APPLICATIONS

- Converters
- Inverters
- Switching regulators
- Motor control systems.

### PINNING

| PIN | DESCRIPTION                           |
|-----|---------------------------------------|
| 1   | base                                  |
| 2   | collector; connected to mounting base |
| 3   | emitter                               |

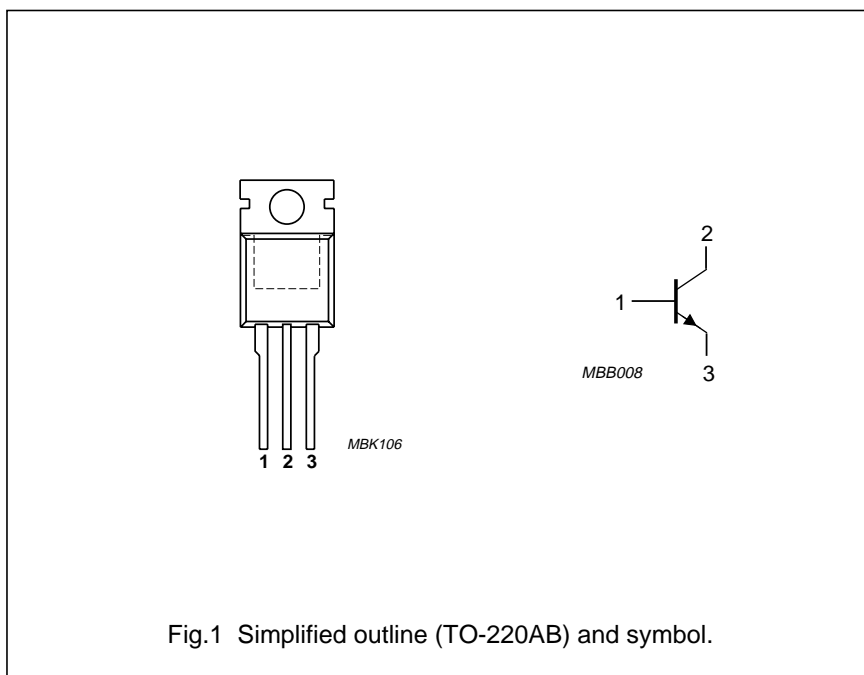


Fig.1 Simplified outline (TO-220AB) and symbol.

### QUICK REFERENCE DATA

| SYMBOL             | PARAMETER                            | CONDITIONS                         | MAX. | UNIT |
|--------------------|--------------------------------------|------------------------------------|------|------|
| V <sub>CESM</sub>  | collector-emitter peak voltage       | V <sub>BE</sub> = 0                | 850  | V    |
|                    | BUT11                                |                                    |      |      |
|                    | BUT11A                               |                                    | 1000 | V    |
| V <sub>CEO</sub>   | collector-emitter voltage            | open base                          | 400  | V    |
|                    | BUT11                                |                                    |      |      |
|                    | BUT11A                               |                                    | 450  | V    |
| V <sub>CEsat</sub> | collector-emitter saturation voltage | see Figs 7 and 9                   | 1.5  | V    |
| I <sub>C</sub>     | collector current (DC)               | see Figs 2 and 4                   | 5    | A    |
| I <sub>CM</sub>    | collector current (peak value)       | see Fig. 4                         | 10   | A    |
| P <sub>tot</sub>   | total power dissipation              | T <sub>mb</sub> ≤ 25 °C; see Fig.3 | 100  | W    |
| t <sub>f</sub>     | fall time                            | resistive load; see Figs 11 and 12 | 0.8  | μs   |

### THERMAL CHARACTERISTICS

| SYMBOL               | PARAMETER   | VALUE | UNIT |
|----------------------|---|-------|------|
| R <sub>th j-mb</sub> | thermal resistance from junction to mounting base | 1.25  | K/W  |

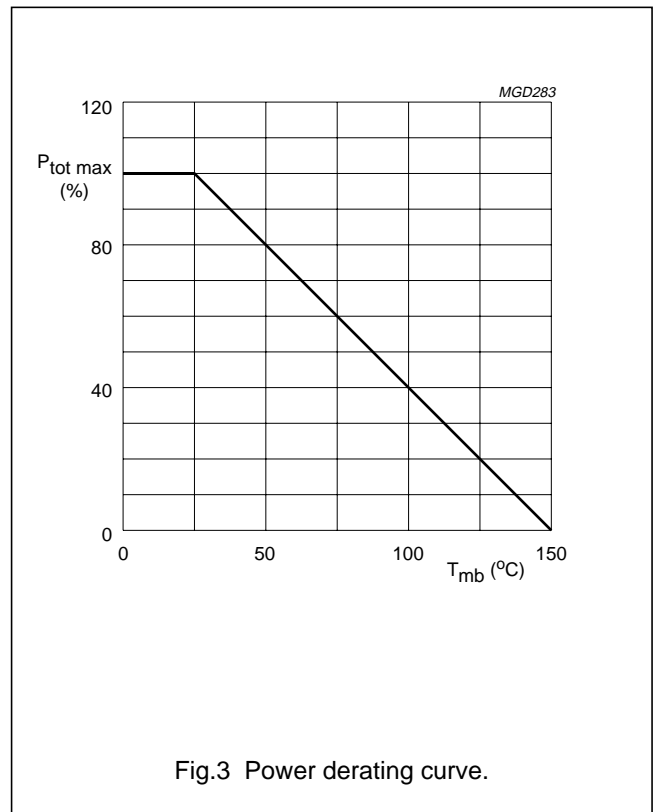
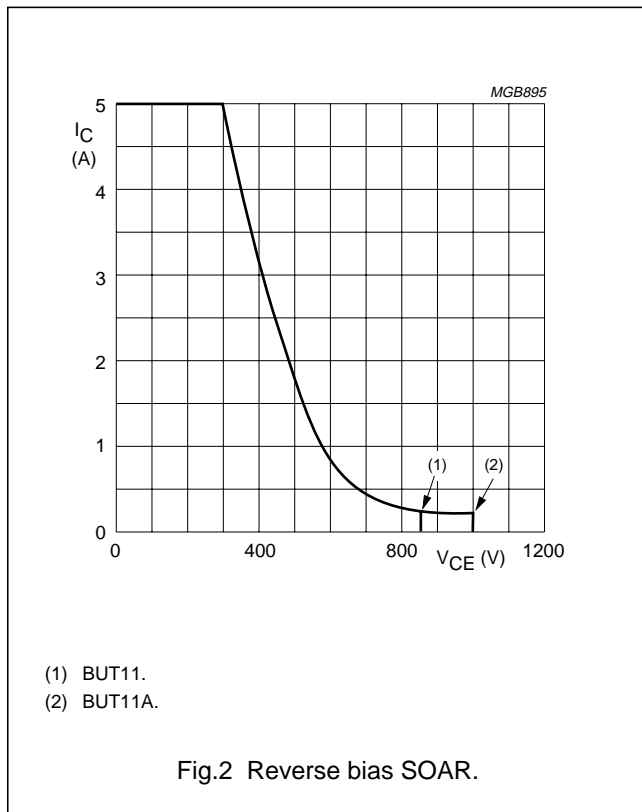
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**LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 134).

| SYMBOL     | PARAMETER                      | CONDITIONS                     | MIN. | MAX. | UNIT |
|------------|--------------------------------|--------------------------------|------|------|------|
| $V_{CESM}$ | collector-emitter peak voltage | $V_{BE} = 0$                   | -    | 850  | V    |
|            | BUT11                          |                                |      | 1000 | V    |
| $V_{CEO}$  | collector-emitter voltage      | open base                      | -    | 400  | V    |
|            | BUT11A                         |                                |      | 450  | V    |
| $I_C$      | collector current (DC)         | see Figs 2 and 4               | -    | 5    | A    |
| $I_{CM}$   | collector current (peak value) | $t_p < 2$ ms; see Fig. 4       | -    | 10   | A    |
| $I_B$      | base current (DC)              |                                | -    | 2    | A    |
| $I_{BM}$   | base current (peak value)      | $t_p < 2$ ms                   | -    | 4    | A    |
| $P_{tot}$  | total power dissipation        | $T_{mb} \leq 25$ °C; see Fig.3 | -    | 100  | W    |
| $T_{stg}$  | storage temperature            |                                | -65  | +150 | °C   |
| $T_j$      | junction temperature           |                                | -    | 150  | °C   |



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## CHARACTERISTICS

$T_j = 25\text{ }^\circ\text{C}$  unless otherwise specified.

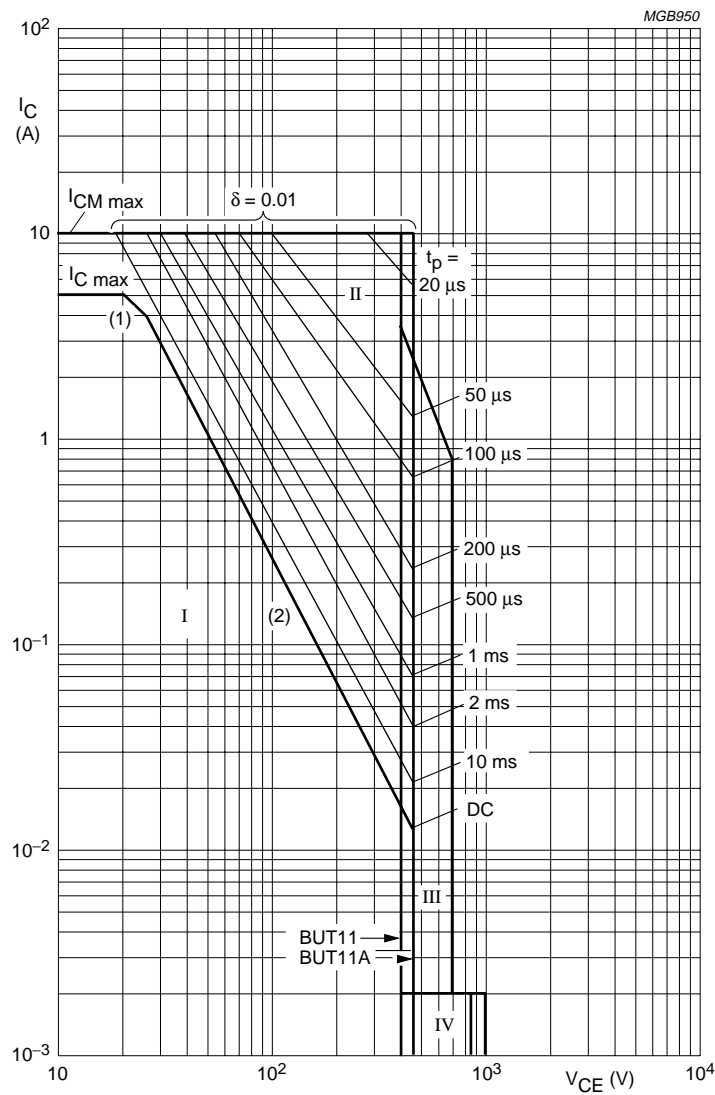
| SYMBOL   | PARAMETER   | CONDITIONS   | MIN. | TYP. | MAX. | UNIT          |
|--|---|--|------|------|------|---------------|
| $V_{CEOsust}$                                      | collector-emitter sustaining voltage<br>BUT11<br>BUT11A | $I_C = 100\text{ mA}$ ; $I_{Boff} = 0$ ; $L = 25\text{ mH}$ ; see Figs 5 and 6           | 400  | –    | –    | V             |
|  |   |  | 450  | –    | –    | V             |
| $V_{CEsat}$  | collector-emitter saturation voltage<br>BUT11<br>BUT11A | $I_C = 3\text{ A}$ ; $I_B = 600\text{ mA}$ ; see Figs 7 and 9                            | –    | –    | 1.5  | V             |
|  |   | $I_C = 2.5\text{ A}$ ; $I_B = 500\text{ mA}$ ; see Figs 7 and 9                          | –    | –    | 1.5  | V             |
| $V_{BEsat}$  | base-emitter saturation voltage<br>BUT11<br>BUT11A      | $I_C = 3\text{ A}$ ; $I_B = 0.6\text{ A}$ ; see Fig.7                                    | –    | –    | 1.3  | V             |
|  |   | $I_C = 2.5\text{ A}$ ; $I_B = 0.5\text{ A}$ ; see Fig.7                                  | –    | –    | 1.3  | V             |
| $I_{CES}$  | collector-emitter cut-off current                       | $V_{CE} = V_{CESMmax}$ ; $V_{BE} = 0$ ; note 1   | –    | –    | 1    | mA            |
|  |   | $V_{CE} = V_{CESMmax}$ ; $V_{BE} = 0$ ; $T_j = 125\text{ }^\circ\text{C}$ ; note 1       | –    | –    | 2    | mA            |
| $I_{EBO}$  | emitter-base cut-off current                            | $V_{EB} = 9\text{ V}$ ; $I_C = 0$  | –    | –    | 10   | mA            |
| $h_{FE}$   | DC current gain   | $V_{CE} = 5\text{ V}$ ; $I_C = 5\text{ mA}$ ; see Fig.10                                 | 10   | 18   | 35   |               |
|  |   | $V_{CE} = 5\text{ V}$ ; $I_C = 500\text{ mA}$ ; see Fig.10                               | 10   | 20   | 35   |               |
| <b>Switching times resistive load (see Fig.12)</b> |   |  |      |      |      |               |
| $t_{on}$   | turn-on time<br>BUT11<br>BUT11A                         | $I_{Con} = 3\text{ A}$ ; $I_{Bon} = -I_{Boff} = 600\text{ mA}$                           | –    | –    | 1    | $\mu\text{s}$ |
|  |   | $I_{Con} = 2.5\text{ A}$ ; $I_{Bon} = -I_{Boff} = 500\text{ mA}$                         | –    | –    | 1    | $\mu\text{s}$ |
| $t_s$  | storage time<br>BUT11<br>BUT11A                         | $I_{Con} = 3\text{ A}$ ; $I_{Bon} = -I_{Boff} = 600\text{ mA}$                           | –    | –    | 4    | $\mu\text{s}$ |
|  |   | $I_{Con} = 2.5\text{ A}$ ; $I_{Bon} = -I_{Boff} = 500\text{ mA}$                         | –    | –    | 4    | $\mu\text{s}$ |
| $t_f$  | fall time<br>BUT11<br>BUT11A                            | $I_{Con} = 3\text{ A}$ ; $I_{Bon} = -I_{Boff} = 600\text{ mA}$                           | –    | –    | 0.8  | $\mu\text{s}$ |
|  |   | $I_{Con} = 2.5\text{ A}$ ; $I_{Bon} = -I_{Boff} = 500\text{ mA}$                         | –    | –    | 0.8  | $\mu\text{s}$ |
| <b>Switching times inductive load (see Fig.14)</b> |   |  |      |      |      |               |
| $t_s$  | storage time<br>BUT11                                   | $I_{Con} = 3\text{ A}$ ; $I_{Bon} = 600\text{ mA}$                                       | –    | 1.1  | 1.4  | $\mu\text{s}$ |
|  |   | $I_{Con} = 3\text{ A}$ ; $I_{Bon} = 600\text{ mA}$ ; $T_j = 100\text{ }^\circ\text{C}$   | –    | 1.2  | 1.5  | $\mu\text{s}$ |
|  | BUT11A  | $I_{Con} = 2.5\text{ A}$ ; $I_{Bon} = 500\text{ mA}$                                     | –    | 1.1  | 1.4  | $\mu\text{s}$ |
|  |   | $I_{Con} = 2.5\text{ A}$ ; $I_{Bon} = 500\text{ mA}$ ; $T_j = 100\text{ }^\circ\text{C}$ | –    | 1.2  | 1.5  | $\mu\text{s}$ |
| $t_f$  | fall time<br>BUT11                                      | $I_{Con} = 3\text{ A}$ ; $I_{Bon} = 600\text{ mA}$                                       | –    | 80   | 150  | ns            |
|  |   | $I_{Con} = 3\text{ A}$ ; $I_{Bon} = 600\text{ mA}$ ; $T_j = 100\text{ }^\circ\text{C}$   | –    | 140  | 300  | ns            |
|  | BUT11A  | $I_{Con} = 2.5\text{ A}$ ; $I_{Bon} = 500\text{ mA}$                                     | –    | 80   | 150  | ns            |
|  |   | $I_{Con} = 2.5\text{ A}$ ; $I_{Bon} = 500\text{ mA}$ ; $T_j = 100\text{ }^\circ\text{C}$ | –    | 140  | 300  | ns            |

## Note

1. Measured with a half-sinewave voltage (curve tracer).

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$T_{mb} \leq 25\text{ }^{\circ}\text{C}$ .

I - Region of permissible DC operation.

II - Permissible extension for repetitive pulse operation.

III - Area of permissible operation during turn-on in single transistor converters, provided  $R_{BE} \leq 100\ \Omega$  and  $t_p \leq 0.6\ \mu\text{s}$ .

IV - Repetitive pulse operation in this region is permissible provided  $V_{BE} \leq 0$  and  $t_p \leq 5\ \text{ms}$ .

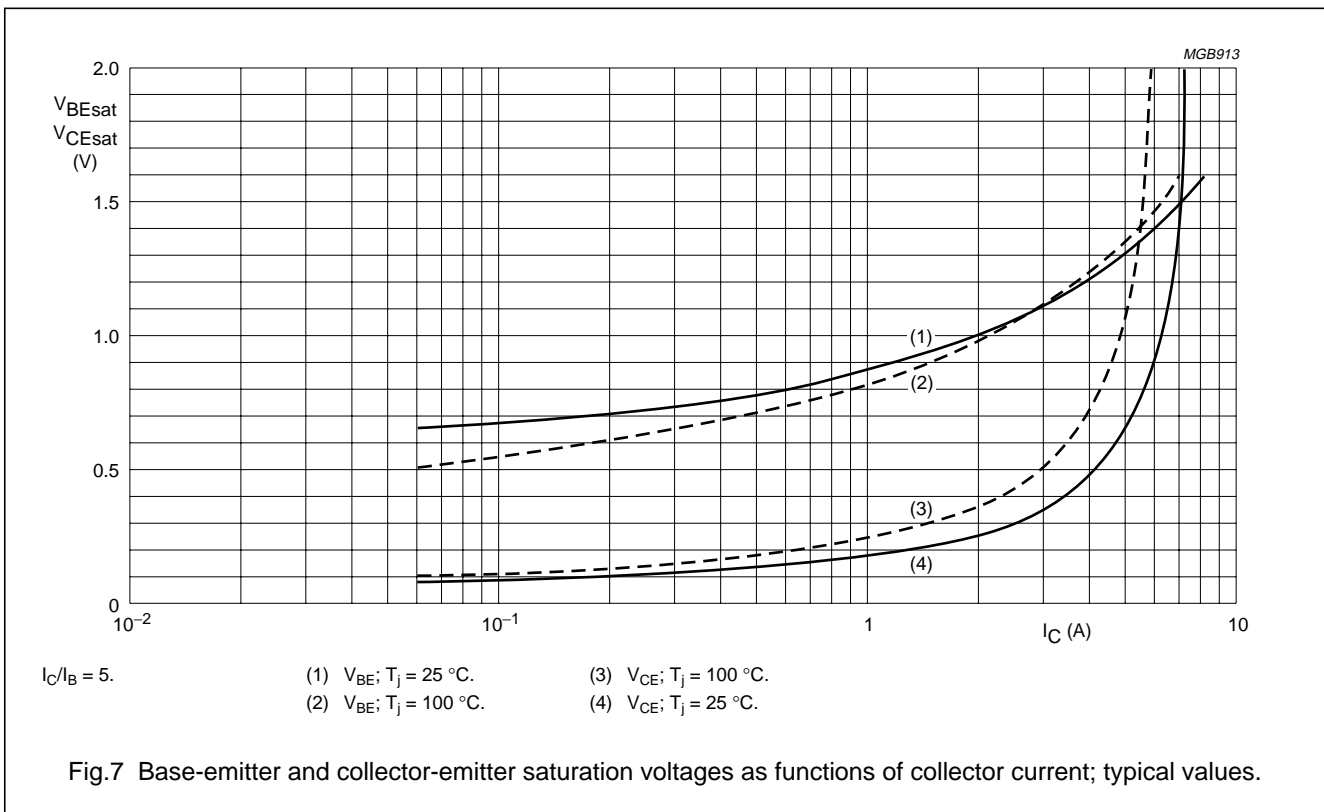
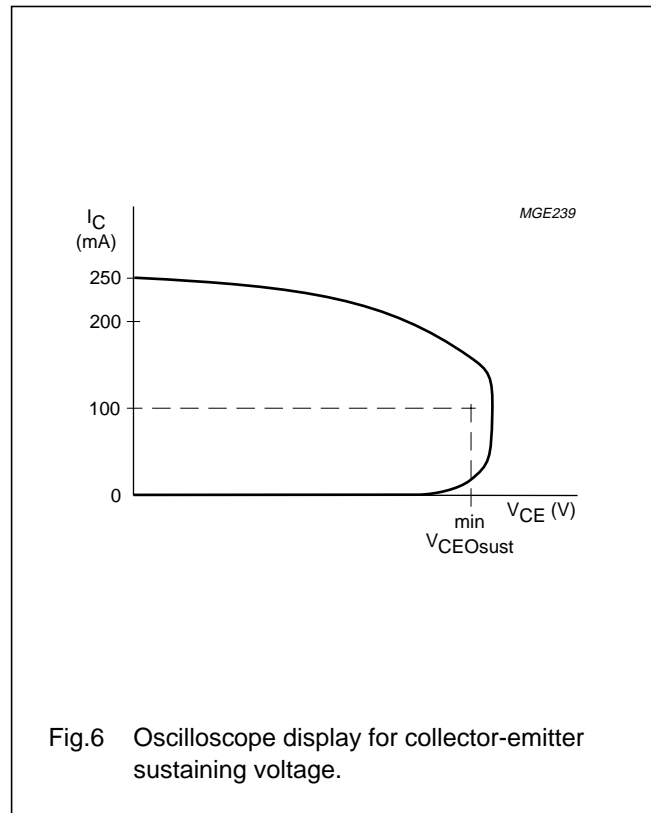
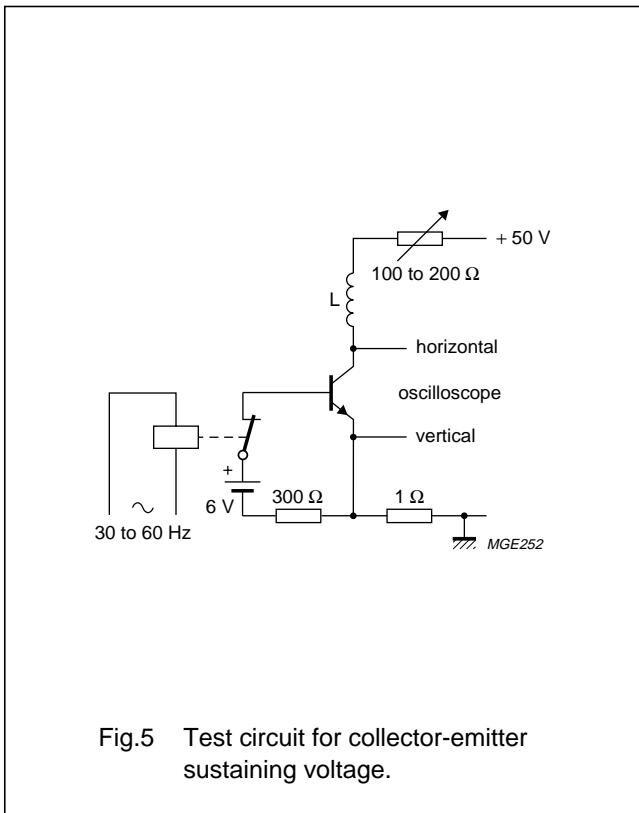
(1)  $P_{tot\ max}$  and  $P_{tot\ peak\ max}$  lines.

(2) Second breakdown limits.

Fig.4 Forward bias SOAR.

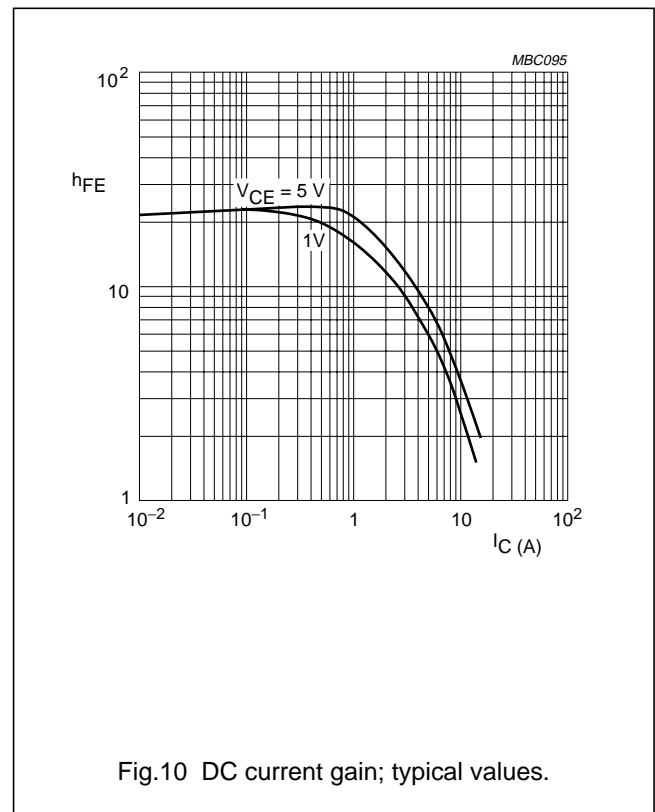
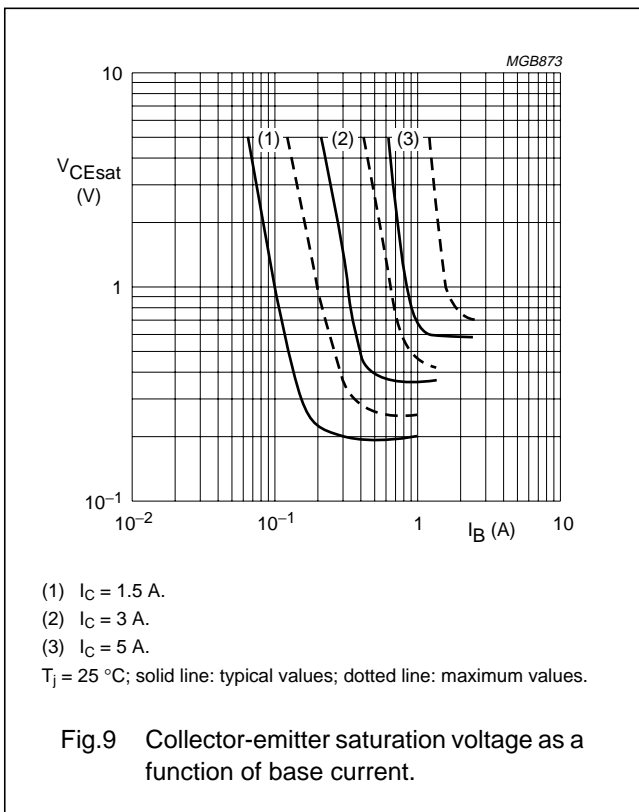
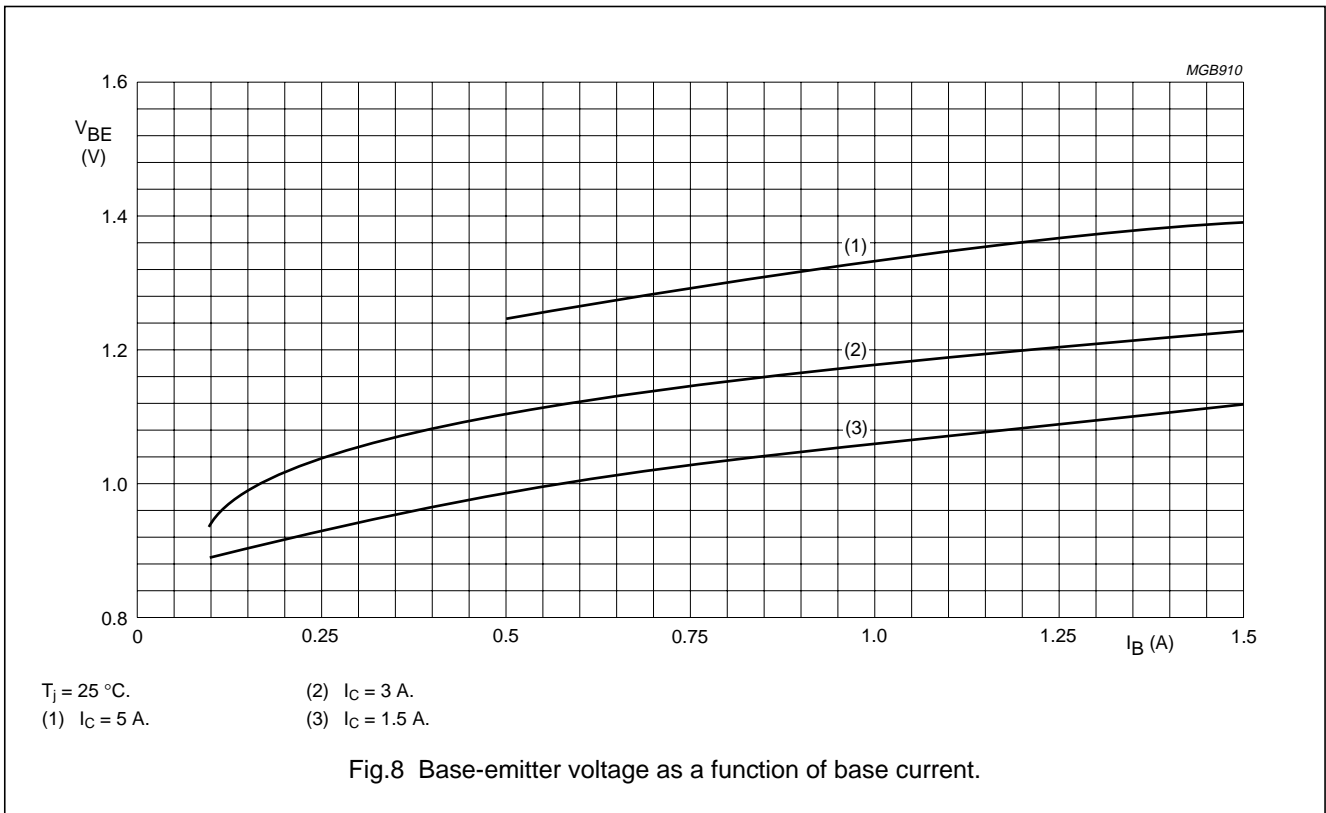
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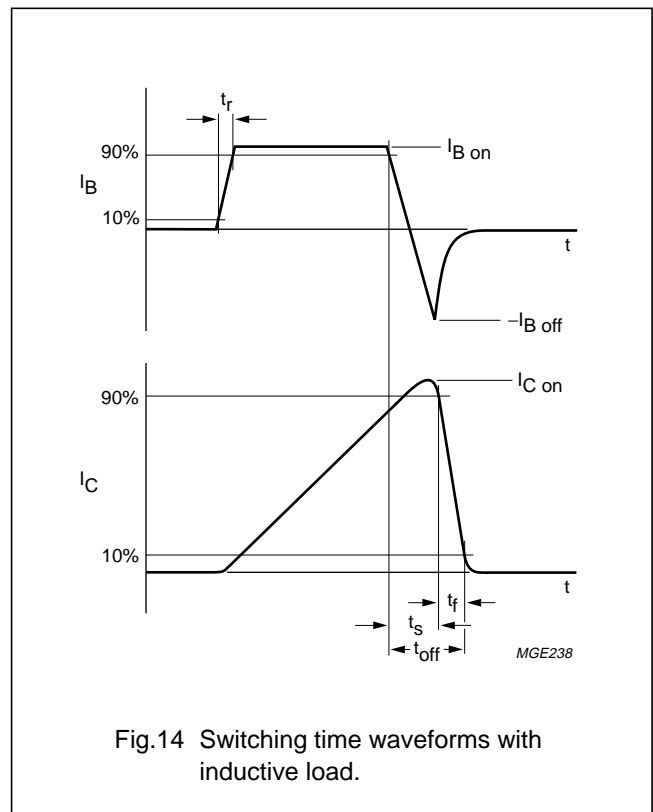
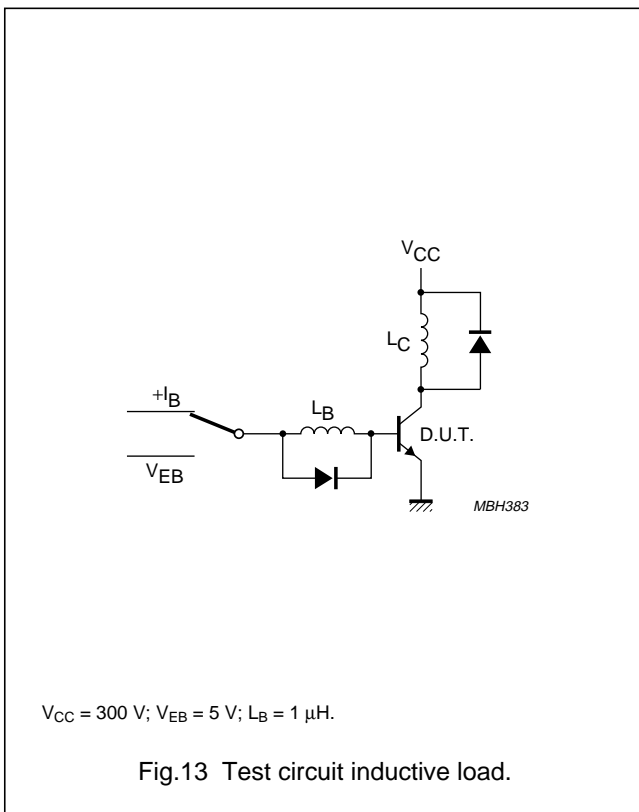
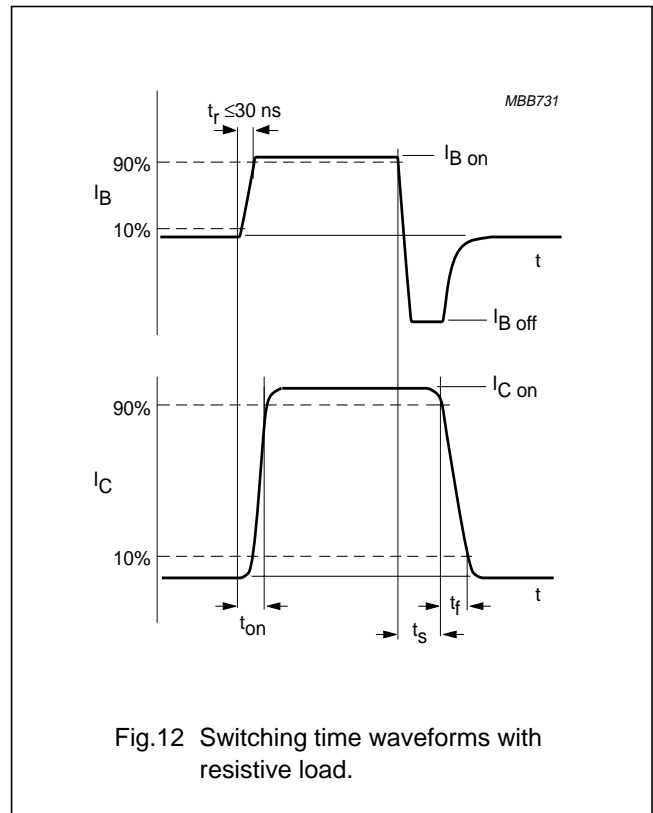
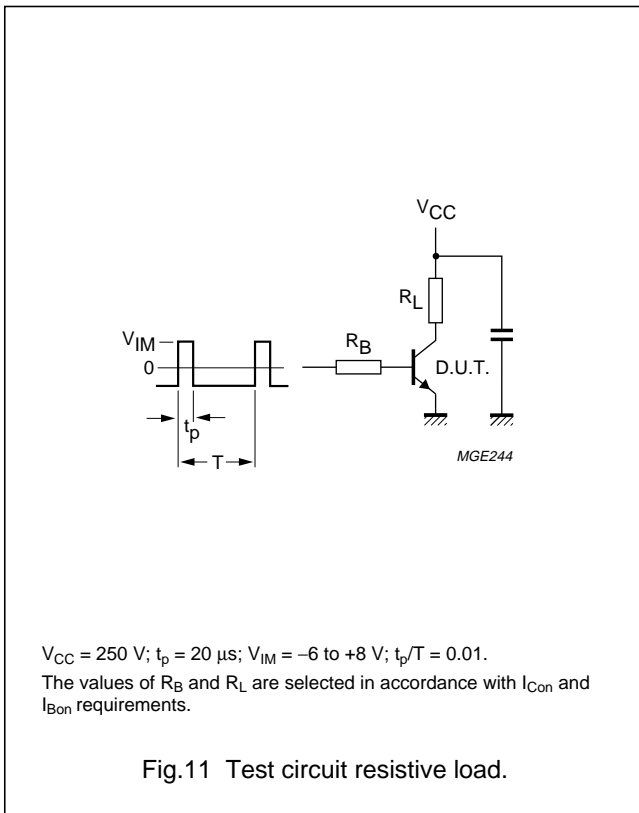
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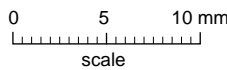
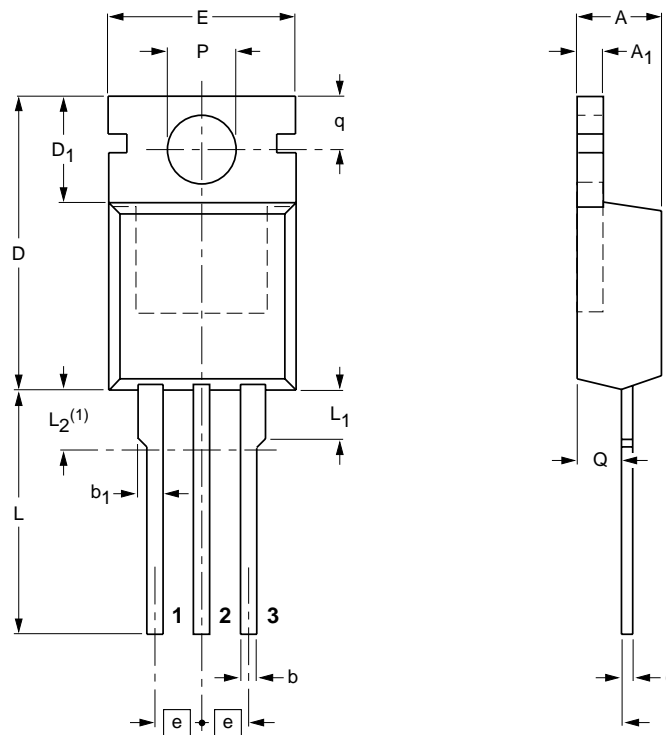
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PACKAGE OUTLINE

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220

SOT78



DIMENSIONS (mm are the original dimensions)

| UNIT | A          | A <sub>1</sub> | b          | b <sub>1</sub> | c          | D            | D <sub>1</sub> | E           | e    | L            | L <sub>1</sub> | L <sub>2</sub> <sup>(1)</sup><br>max. | P          | q          | Q          |
|------|------------|----------------|------------|----------------|------------|--------------|----------------|-------------|------|--------------|----------------|---------------------------------------|------------|------------|------------|
| mm   | 4.5<br>4.1 | 1.39<br>1.27   | 0.9<br>0.7 | 1.3<br>1.0     | 0.7<br>0.4 | 15.8<br>15.2 | 6.4<br>5.9     | 10.3<br>9.7 | 2.54 | 15.0<br>13.5 | 3.30<br>2.79   | 3.0                                   | 3.8<br>3.6 | 3.0<br>2.7 | 2.6<br>2.2 |

Note

1. Terminals in this zone are not tinned.

| OUTLINE<br>VERSION | REFERENCES |        |      |  | EUROPEAN<br>PROJECTION | ISSUE DATE |
|--------------------|------------|--------|------|--|------------------------|------------|
|                    | IEC        | JEDEC  | EIAJ |  |                        |            |
| SOT78              |            | TO-220 |      |  |                        | 97-06-11   |

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**DEFINITIONS**

| <b>Data sheet status</b>  |   |
|---|---|
| Objective specification   | This data sheet contains target or goal specifications for product development.       |
| Preliminary specification   | This data sheet contains preliminary data; supplementary data may be published later. |
| Product specification   | This data sheet contains final product specifications.                                |
| <b>Limiting values</b>  |   |
| Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability. |   |
| <b>Application information</b>  |   |
| Where application information is given, it is advisory and does not form part of the specification.   |   |

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Fax. +43 160 101 1210

**Belarus:** Hotel Minsk Business Center, Bld. 3, r. 1211, Volodarski Str. 6,  
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**Colombia:** see South America

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**Denmark:** Prags Boulevard 80, PB 1919, DK-2300 COPENHAGEN S,  
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**Finland:** Sinikalliontie 3, FIN-02630 ESPOO,  
Tel. +358 9 615800, Fax. +358 9 61580920

**France:** 4 Rue du Port-aux-Vins, BP317, 92156 SURESNES Cedex,  
Tel. +33 1 40 99 6161, Fax. +33 1 40 99 6427

**Germany:** Hammerbrookstraße 69, D-20097 HAMBURG,  
Tel. +49 40 23 53 60, Fax. +49 40 23 536 300

**Greece:** No. 15, 25th March Street, GR 17778 TAVROS/ATHENS,  
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**Hungary:** see Austria

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**Indonesia:** see Singapore

**Ireland:** Newstead, Clonskeagh, DUBLIN 14,  
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**Israel:** RAPAC Electronics, 7 Kehilat Saloniki St, PO Box 18053,  
TEL AVIV 61180, Tel. +972 3 645 0444, Fax. +972 3 649 1007

**Italy:** PHILIPS SEMICONDUCTORS, Piazza IV Novembre 3,  
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**Malaysia:** No. 76 Jalan Universiti, 46200 PETALING JAYA, SELANGOR,  
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**Mexico:** 5900 Gateway East, Suite 200, EL PASO, TEXAS 79905,  
Tel. +9-5 800 234 7381

**Middle East:** see Italy

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**New Zealand:** 2 Wagener Place, C.P.O. Box 1041, AUCKLAND,  
Tel. +64 9 849 4160, Fax. +64 9 849 7811

**Norway:** Box 1, Manglerud 0612, OSLO,  
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**Philippines:** Philips Semiconductors Philippines Inc.,  
106 Valero St. Salcedo Village, P.O. Box 2108 MCC, MAKATI,  
Metro MANILA, Tel. +63 2 816 6380, Fax. +63 2 817 3474

**Poland:** Ul. Lukiska 10, PL 04-123 WARSZAWA,  
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**South America:** Rua do Rocio 220, 5th floor, Suite 51,  
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Tel. +55 11 821 2333, Fax. +55 11 829 1849

**Spain:** Balmes 22, 08007 BARCELONA,  
Tel. +34 3 301 6312, Fax. +34 3 301 4107

**Sweden:** Kottbygatan 7, Akalla, S-16485 STOCKHOLM,  
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**Taiwan:** Philips Semiconductors, 6F, No. 96, Chien Kuo N. Rd., Sec. 1,  
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**Thailand:** PHILIPS ELECTRONICS (THAILAND) Ltd.,  
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**Turkey:** Talatpasa Cad. No. 5, 80640 GÜLTEPE/ISTANBUL,  
Tel. +90 212 279 2770, Fax. +90 212 282 6707

**Ukraine:** PHILIPS UKRAINE, 4 Patrice Lumumba str., Building B, Floor 7,  
252042 KIEV, Tel. +380 44 264 2776, Fax. +380 44 268 0461

**United Kingdom:** Philips Semiconductors Ltd., 276 Bath Road, Hayes,  
MIDDLESEX UB3 5BX, Tel. +44 181 730 5000, Fax. +44 181 754 8421

**United States:** 811 East Arques Avenue, SUNNYVALE, CA 94088-3409,  
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